

IN THE SPECIFICATION:

Please replace the paragraph beginning on line 25 of page 15 with the following amended paragraph:

a' As shown in Figs. 2A and 3 (plan view), the DASi film is then annealed to form a polysilicon film, and the polysilicon film and the ONO film 6 are patterned by photolithography and subsequent dry etching, thereby forming bandshape word lines 7 that perpendicularly cross the bit lines 5 with the ONO film 6 being interposed between them and serve also as gate electrodes. At this time, a tungsten silicide (WSi) film may be formed on the polysilicon film to form word lines having a polycide structure and thereby decrease the resistance of electrical interconnections.